

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D $T_A = +25^\circ C$
150V	310m Ω @ $V_{GS} = 10V$	2.0A
	330m Ω @ $V_{GS} = 5.0V$	1.9A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- Transformer Driving Switch
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features

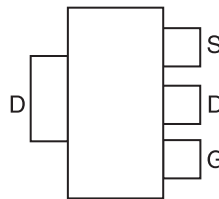
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Fast Switching Speed
- Low On-Resistance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

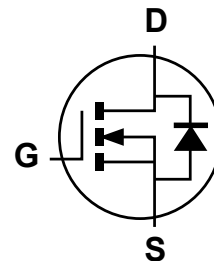
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.112 grams (Approximate)



Top View



Pin Out - Top View



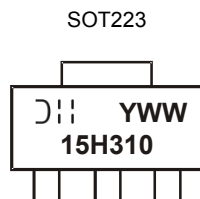
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
DMN15H310SE-13	Standard	SOT223	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



$\text{D}||$ = Manufacturer's Marking
 15H310 = Marking Code
 YWW = Date Code Marking
 Y or Y = Year (ex: 4 = 2014)
 WW = Week (01 - 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	150	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	I _D	T _A = +25°C	2.0
		T _A = +70°C	1.6
	I _D	T _C = +25°C	7.1
		T _C = +70°C	5.6
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I _{DM}	10	A
Maximum Body Diode Continuous Current	I _S	2.5	A
Avalanche Energy (Note 6) L=26mH	E _{AS}	1.45	mJ
Avalanche Current (Note 6) L=26mH	I _{AS}	0.2	A
Peak Diode Recovery dv/dt (I _{SD} ≤ 7.3A, di/dt ≤ 300A/µs)	dv/dt	5	V/ns

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	1.9
		T _A = +70°C	1.2
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	64	°C/W
Total Power Dissipation (Note 5)	P _D	23.5	W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	5.3	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	150	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	µA	V _{DS} = 120V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1	2.2	3	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(on)}	—	178	310	mΩ	V _{GS} = 10V, I _D = 1.5A
		—	190	330		V _{GS} = 5.0V, I _D = 1.0A
Diode Forward Voltage	V _{SD}	—	0.76	1.2	V	V _{GS} = 0V, I _S = 1.7A
DYNAMIC CHARACTERISTICS (Note 6)						
Input Capacitance	C _{iss}	—	405	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	40	—		
Reverse Transfer Capacitance	C _{rss}	—	20	—		
Gate Resistance	R _G	—	2.88	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 5.0V)	Q _g	—	4.6	—	nC	V _{DS} = 80V, I _D = 7.3A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	8.7	—		
Gate-Source Charge	Q _{gs}	—	1.7	—		
Gate-Drain Charge	Q _{gd}	—	1.8	—		
Turn-On Delay Time	t _{D(on)}	—	3.5	—	nS	V _{DD} = 50V, V _{GS} = 10V, R _G = 25Ω, I _D = 7.3A
Turn-On Rise Time	t _r	—	7.8	—		
Turn-Off Delay Time	t _{D(off)}	—	22	—		
Turn-Off Fall Time	t _f	—	11	—		
Reverse Recovery Time	t _{rr}	—	38	—	ns	I _F = 7.3A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{rr}	—	53	—	nC	I _F = 7.3A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 - Guaranteed by design. Not subject to product testing.
 - Short duration pulse test used to minimize self-heating effect.

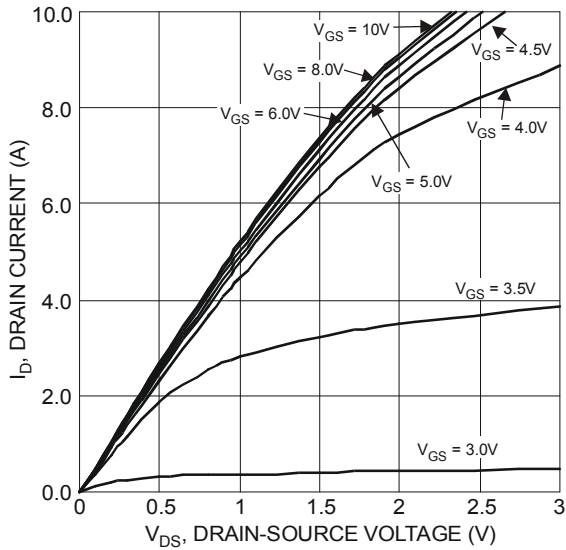


Figure 1 Typical Output Characteristics

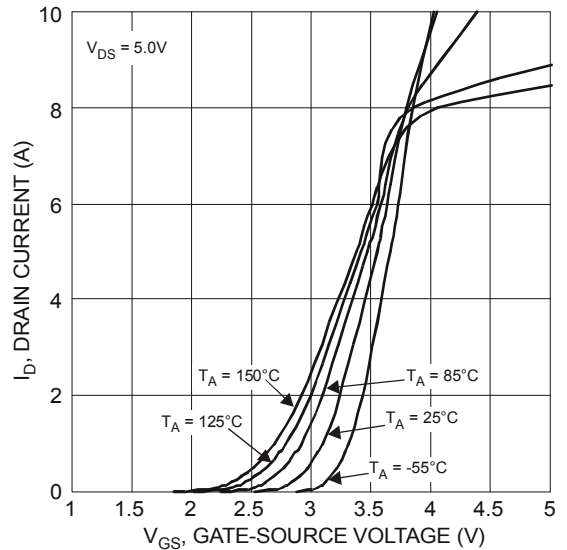


Figure 2 Typical Transfer Characteristics

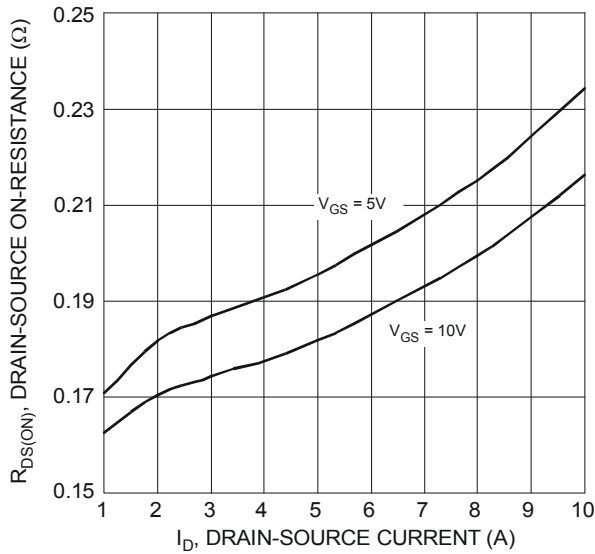


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

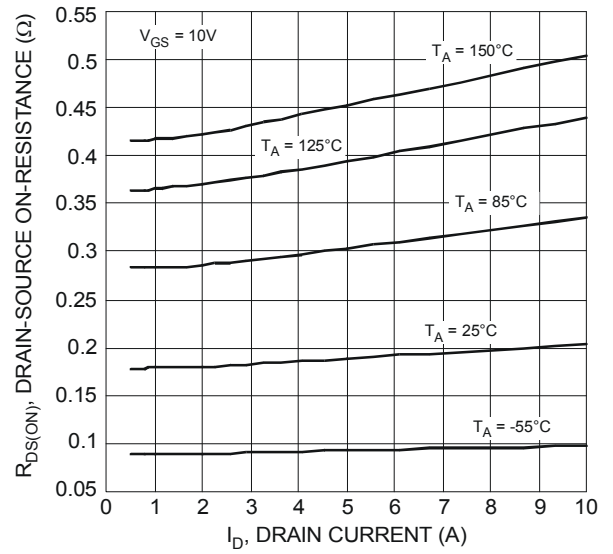


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

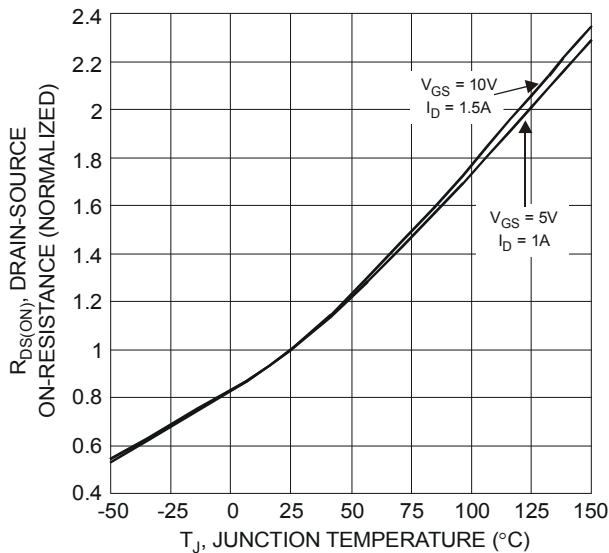


Figure 5 On-Resistance Variation with Temperature

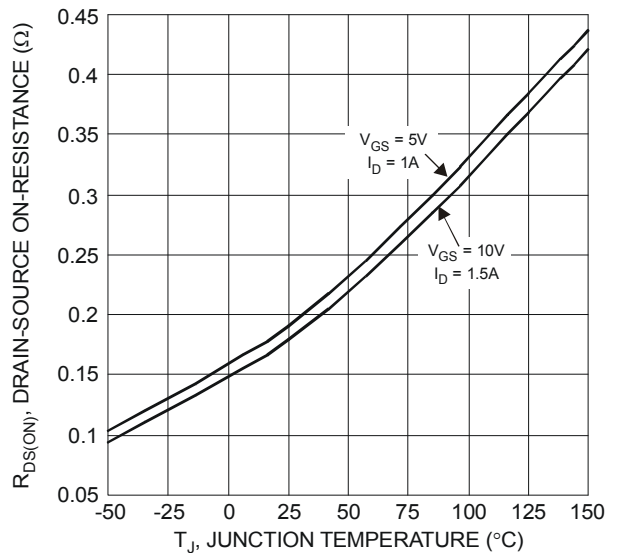


Figure 6 On-Resistance Variation with Temperature

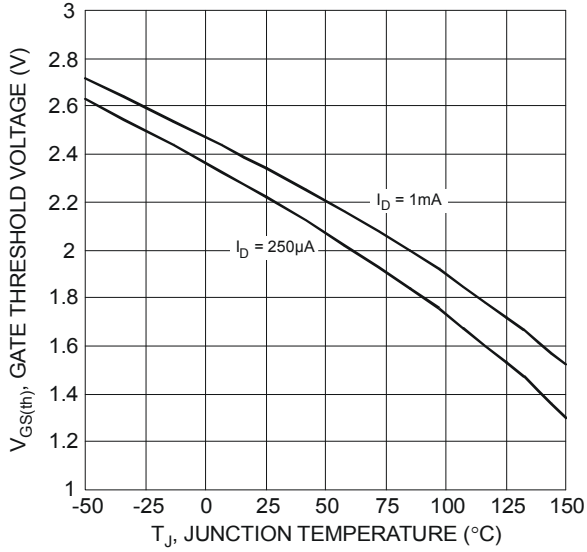


Figure 7 Gate Threshold Variation vs. Ambient Temperature

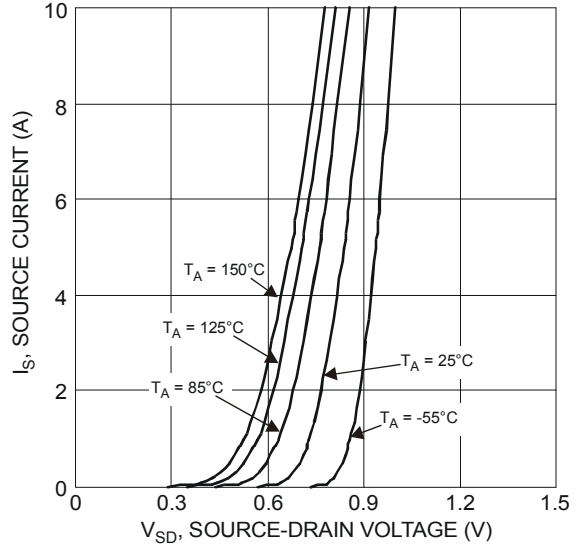


Figure 8 Diode Forward Voltage vs. Current

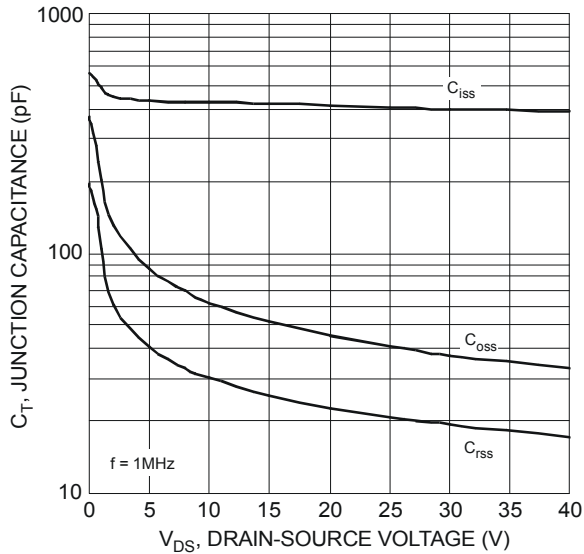


Figure 9 Typical Junction Capacitance

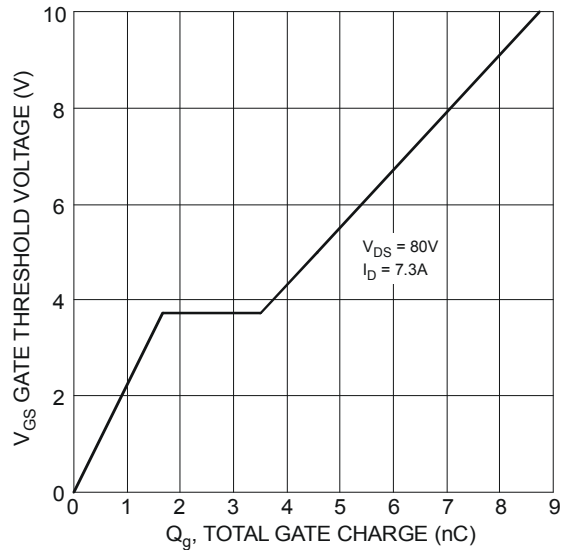


Figure 10 Gate Charge

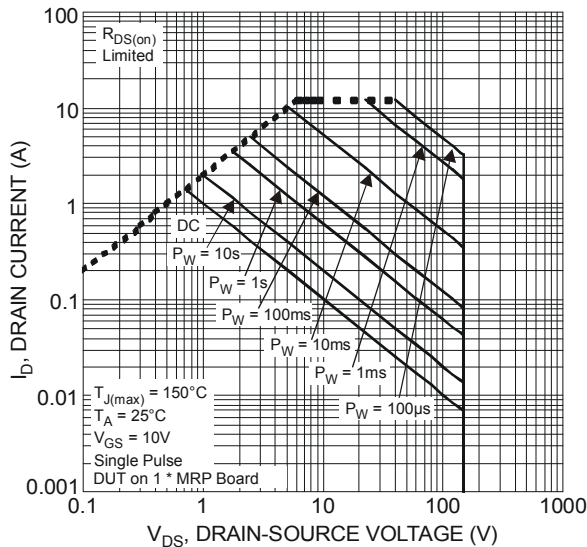


Figure 11 SOA, Safe Operation Area

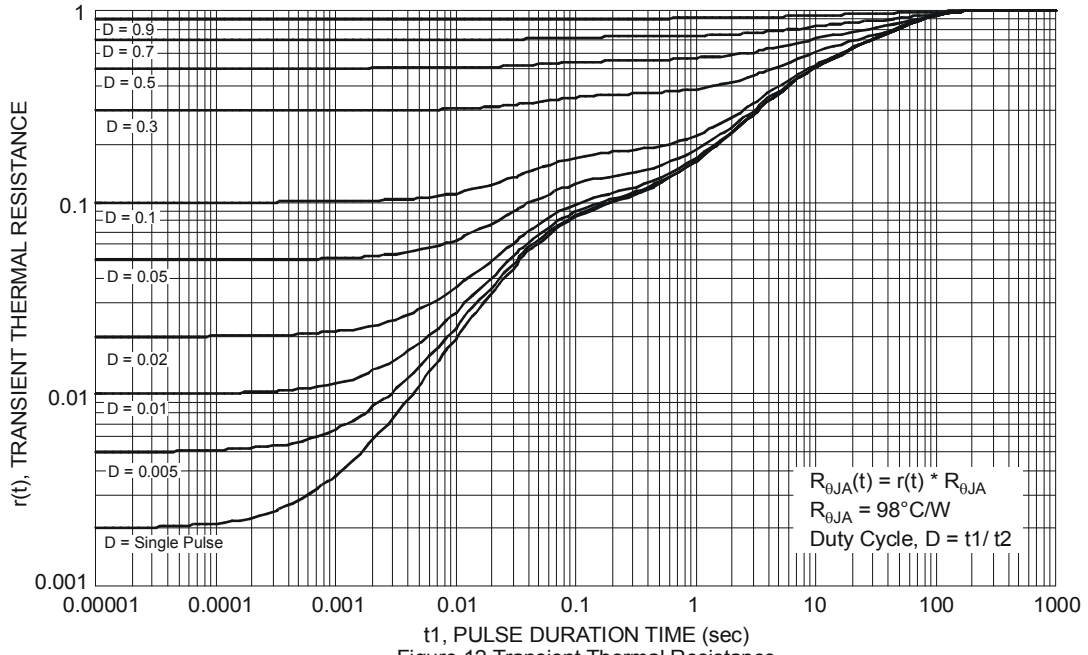
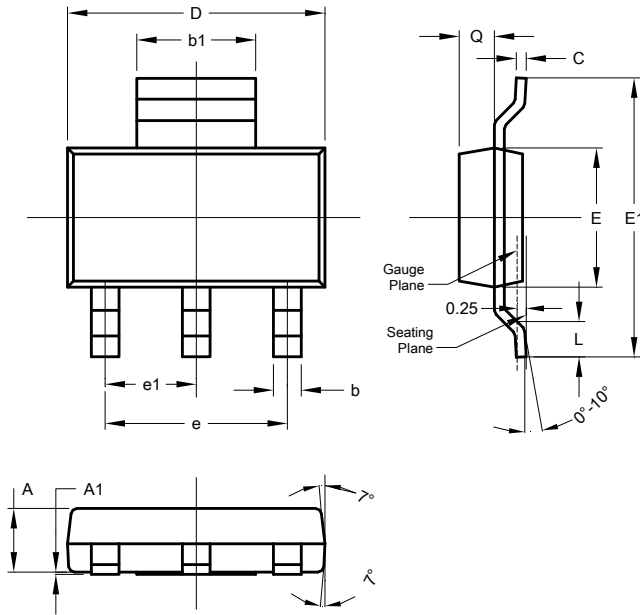


Figure 12 Transient Thermal Resistance

Package Outline Dimensions

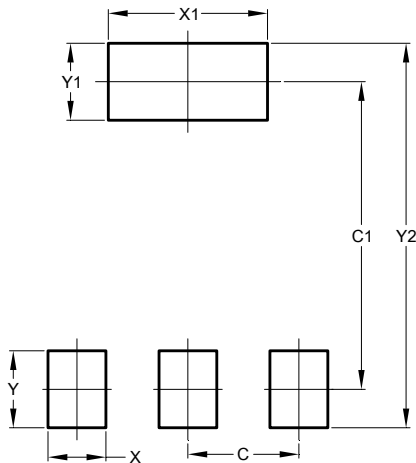
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00

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